Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.0 1.5	A
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.5 2.0	A
Maximum Body Diode Forward Current (Note 5)			I_S	2.0	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	12	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.8	W
	T_A = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	157	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.15	W
	T_A = +70°C		0.7	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	110	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	69	85	mΩ	V_{GS} = 10V, I_D = 3.2A
			75	120		V_{GS} = 4.5V, I_D = 2.8A
Diode Forward Voltage	V_{SD}	—	—	1.2	V	V_{GS} = 0V, I_S = 2.5A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	606	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	32.6	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	24.6	—	pF	
Gate Resistance	R_g	—	1.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 10V)	Q_g	—	12.3	—	nC	V_{DS} = 30V, I_D = 3A
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	5.6	—	nC	
Gate-Source Charge	Q_{gs}	—	1.7	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.9	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.5	—	ns	V_{GS} = 10V, V_{DS} = 30V, R_g = 20Ω, R_L = 50Ω
Turn-On Rise Time	t_R	—	4.1	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	35	—	ns	
Turn-Off Fall Time	t_F	—	11	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

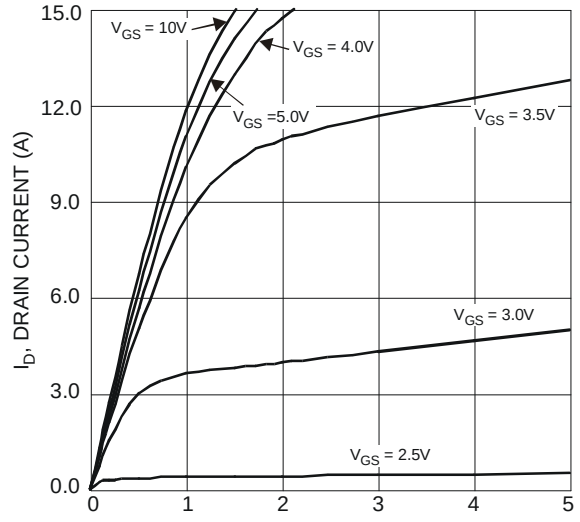


Figure 1 Typical Output Characteristics

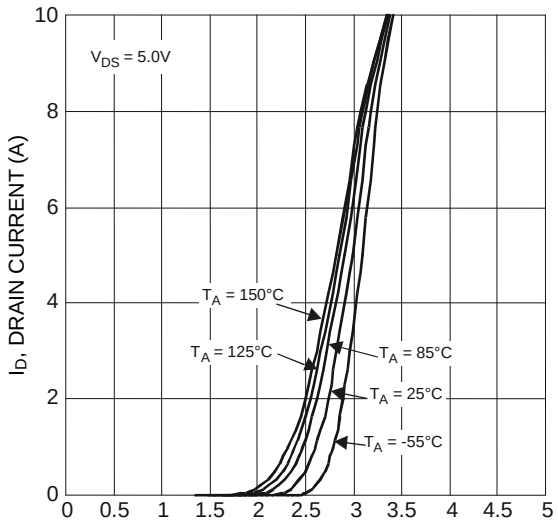


Figure 2 Typical Transfer Characteristics

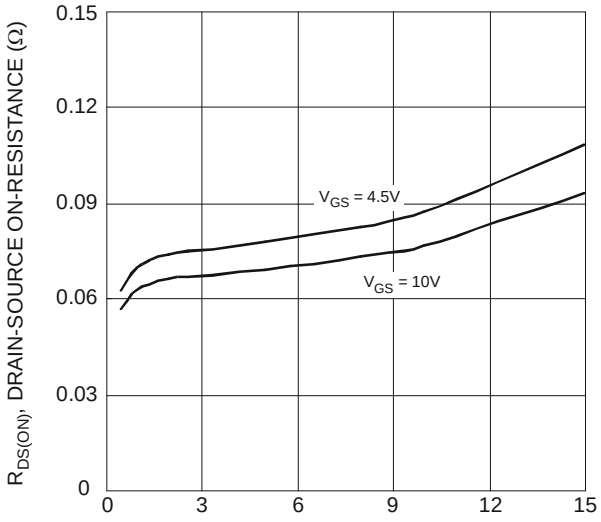


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

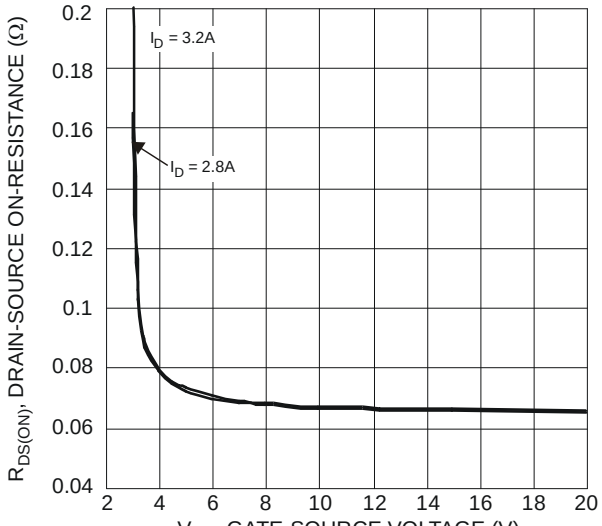


Figure 4 Typical Transfer Characteristics

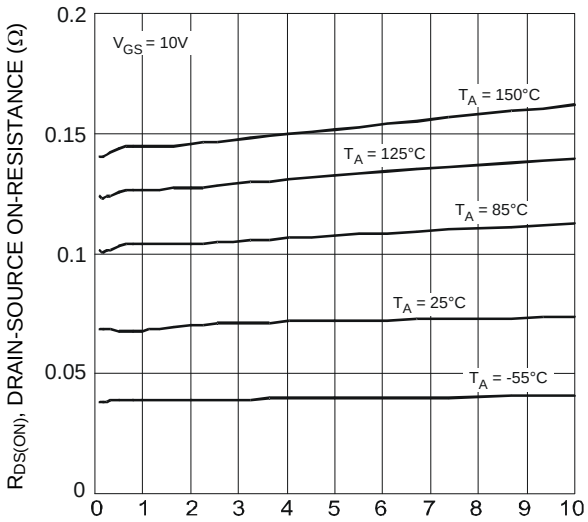


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

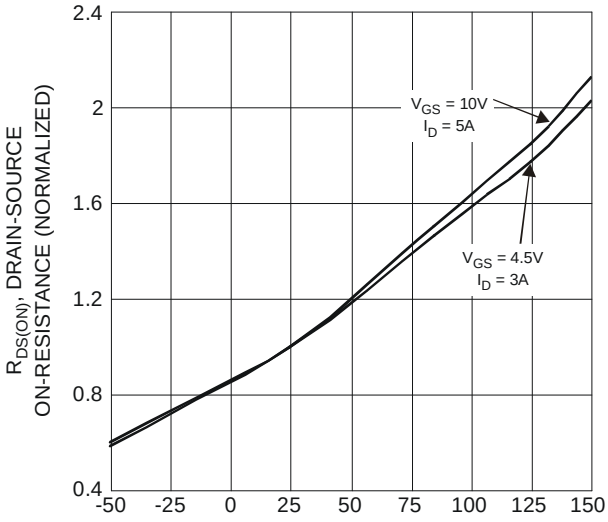


Figure 6 On-Resistance Variation with Temperature

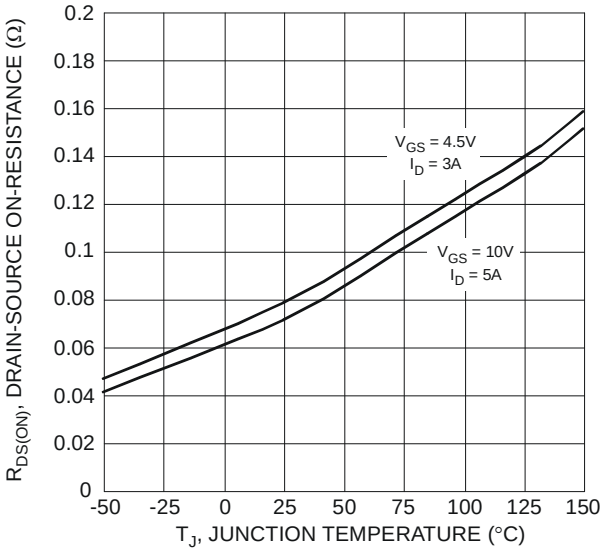


Figure 7 On-Resistance Variation with Temperature

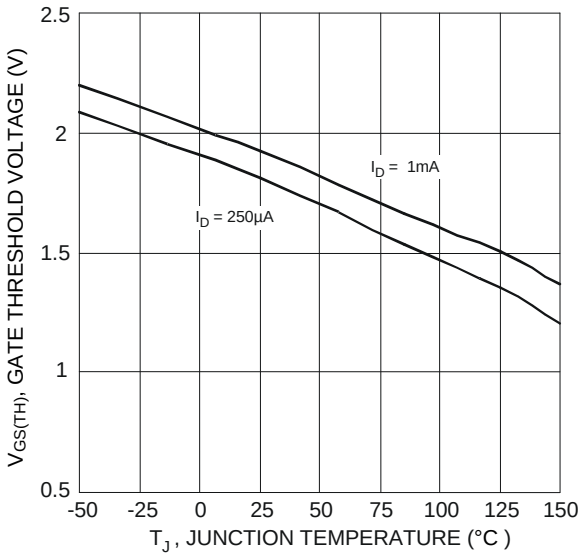


Figure 8 Gate Threshold Variation vs. Junction Temperature

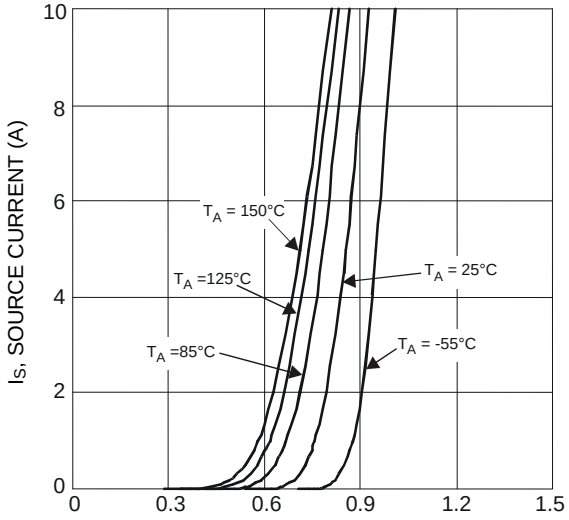


Figure 9 Diode Forward Voltage vs. Current

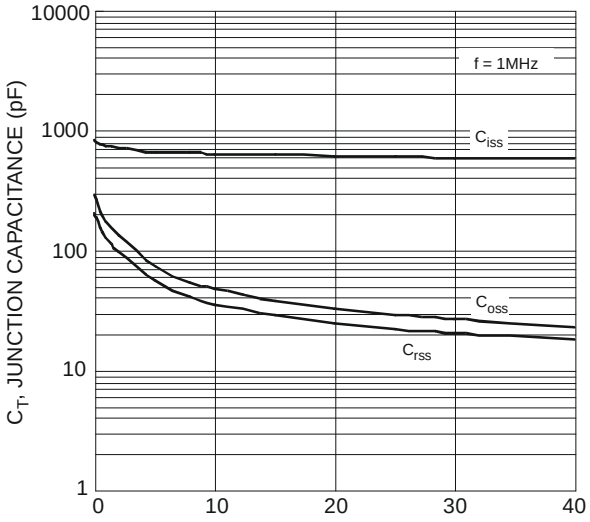


Figure 10 Typical Junction Capacitance

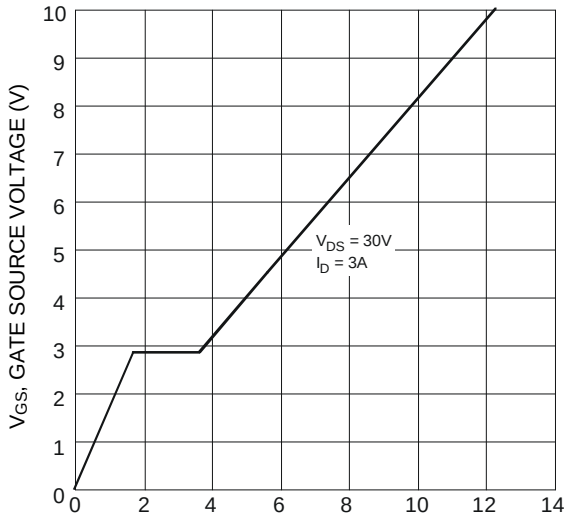


Figure 11 Gate Charge

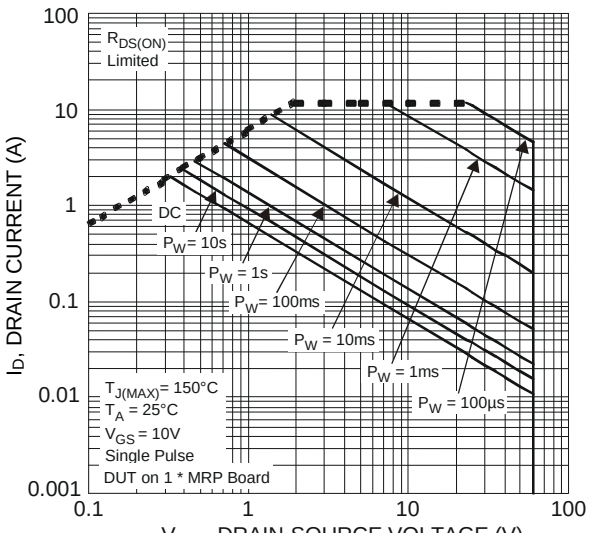


Figure 12 SOA, Safe Operation Area

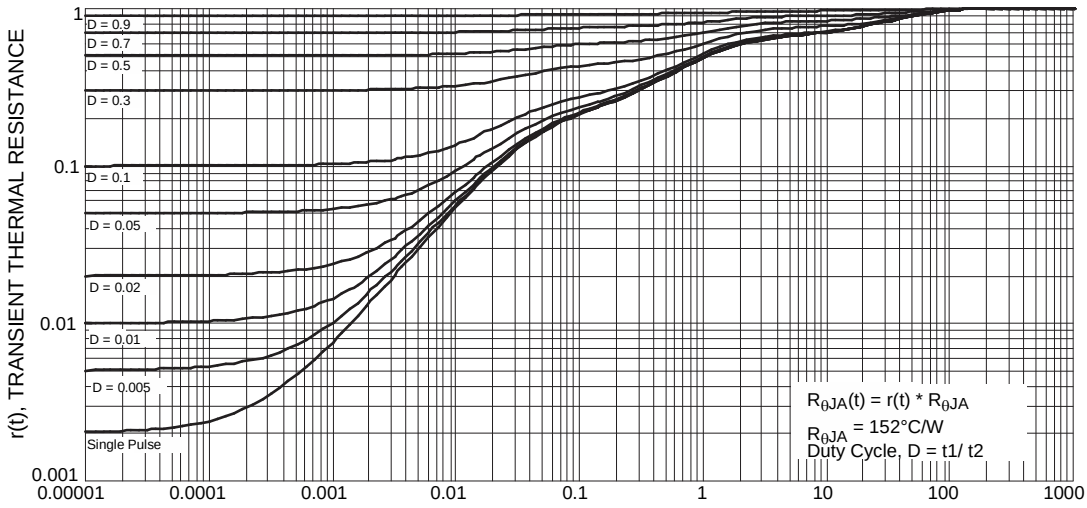
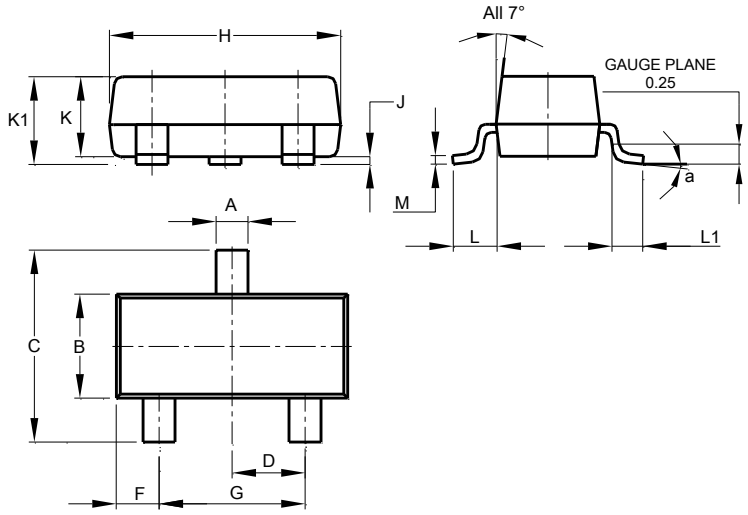


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

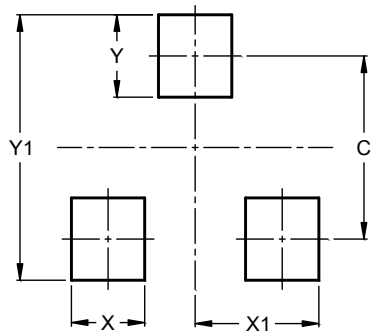


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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